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ACT108-800EEP

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ACT108-800E

AC Thyristor power switch

20 August 2014 **Product data sheet**

1. General description

AC Thyristor power switch in a SOT54 (TO-92) plastic package with self-protective capabilities against low and high energy transients.

2. Features and benefits

- Exclusive negative gate triggering
- Full cycle AC conduction
- Remote gate separates the gate driver from the effects of the load current
- Safe clamping of low energy over-voltage transients
- High voltage capability
- Self-protective turn-on during high energy voltage transients
- Very high noise immunity

3. Applications

- Fan motor circuits
- Pump motor circuits
- Lower-power highly inductive, resistive and safety loads

4. Quick reference data

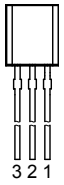
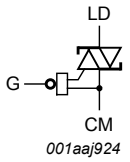
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5		-	-	13	A
T_j	junction temperature			-	-	125	°C
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 75$ °C; Fig. 1; Fig. 2; Fig. 3		-	-	0.8	A
V_{PP}	peak pulse voltage	T_j = 25 °C; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses; Fig. 6		-	-	2.5	kV

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 100 mA; LD+ G-; T_j = 25 °C; Fig. 8		1	-	10	mA
		V_D = 12 V; I_T = 100 mA; LD- G-; T_j = 25 °C; Fig. 8		1	-	10	mA
V_{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C		850	-	-	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 13		500	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit; Fig. 14; Fig. 15		0.5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 **TO-92 (SOT54)**	
2	G	gate		
3	LD	load		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ACT108-800E	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 75$ °C; Fig. 1; Fig. 2; Fig. 3		-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5		-	13	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		-	14.3	A
I^2t	I^2t for fusing	$t_p = 10$ ms; sine-wave pulse		-	0.84	A^2s
dI_T/dt	rate of rise of on-state current	$I_T = 1$ A; $I_G = 20$ mA; $dI_G/dt = 0.2$ A/µs		-	100	A/µs
I_{GM}	peak gate current	t = 20 µs		-	1	A
V_{GM}	peak gate voltage	positive applied gate voltage		-	15	V
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.1	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	125	°C
V_{PP}	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses; Fig. 6		-	2.5	kV

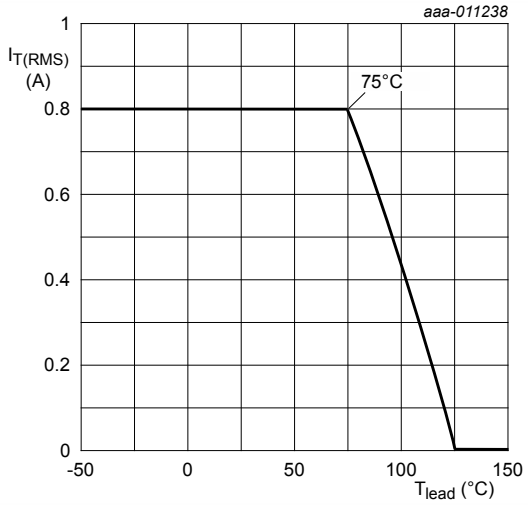
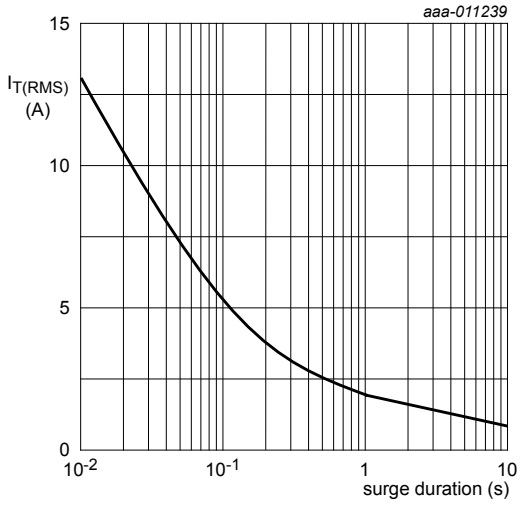
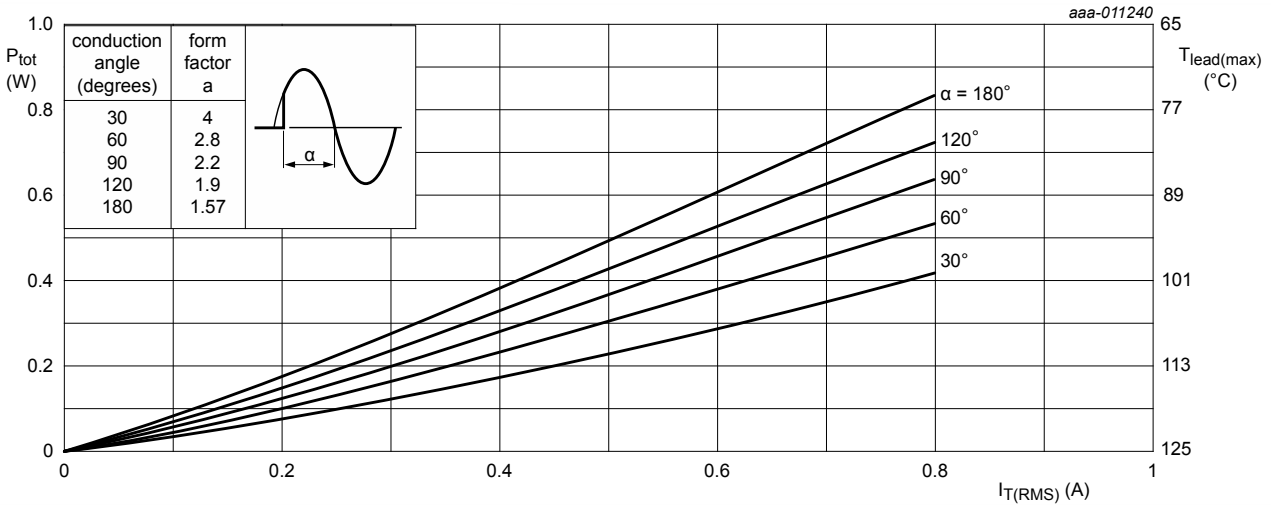


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; T_{lead} = 75 °C

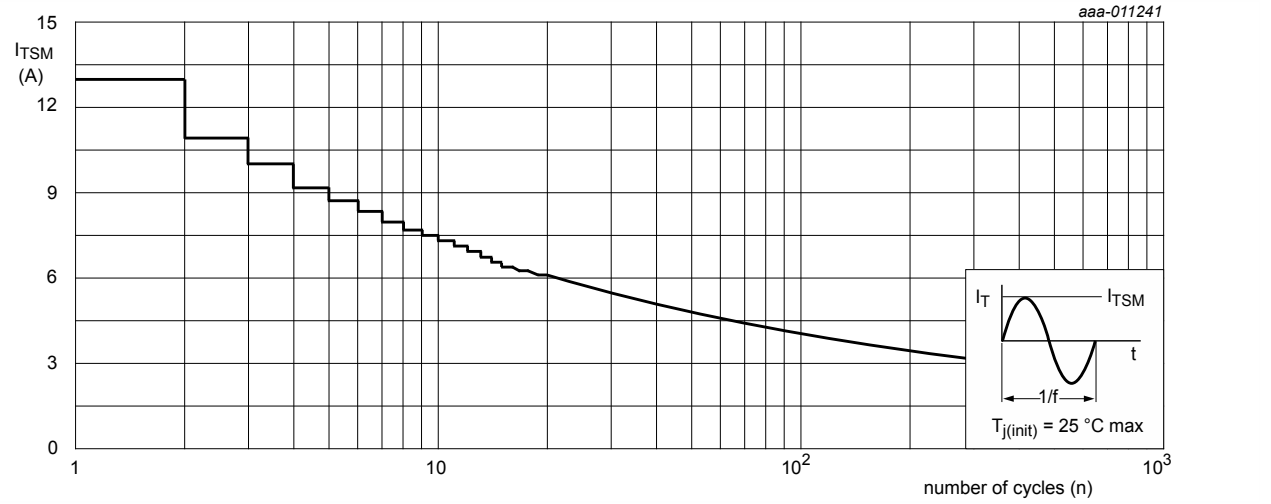
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

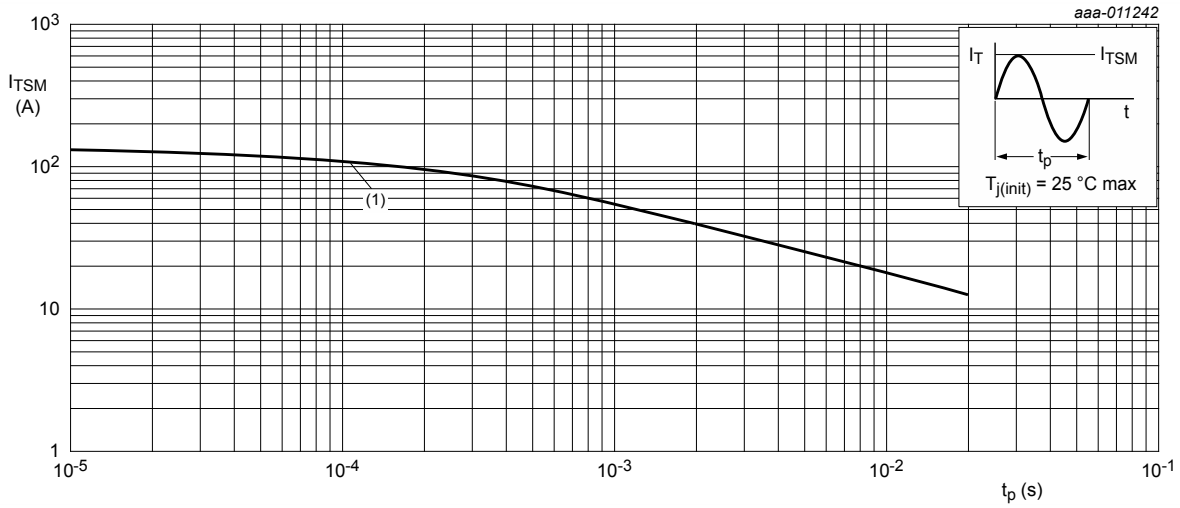
a = form factor = $I_{T(RMS)}/I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20$ ms

(1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

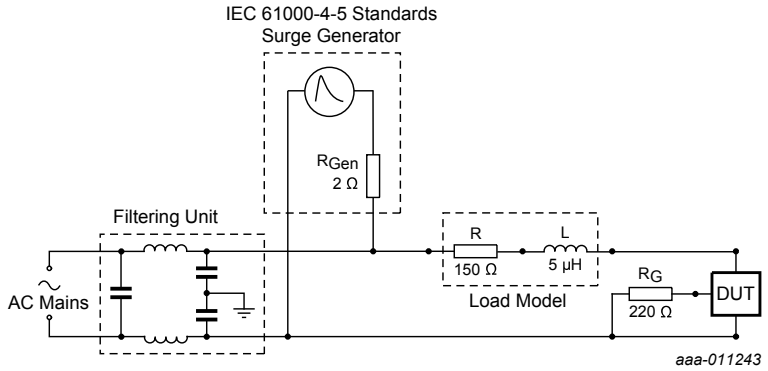


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}lead)}$	thermal resistance from junction to lead	full cycle with heatsink compound; Fig. 7		-	-	60	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted; lead length 4 mm		-	150	-	K/W

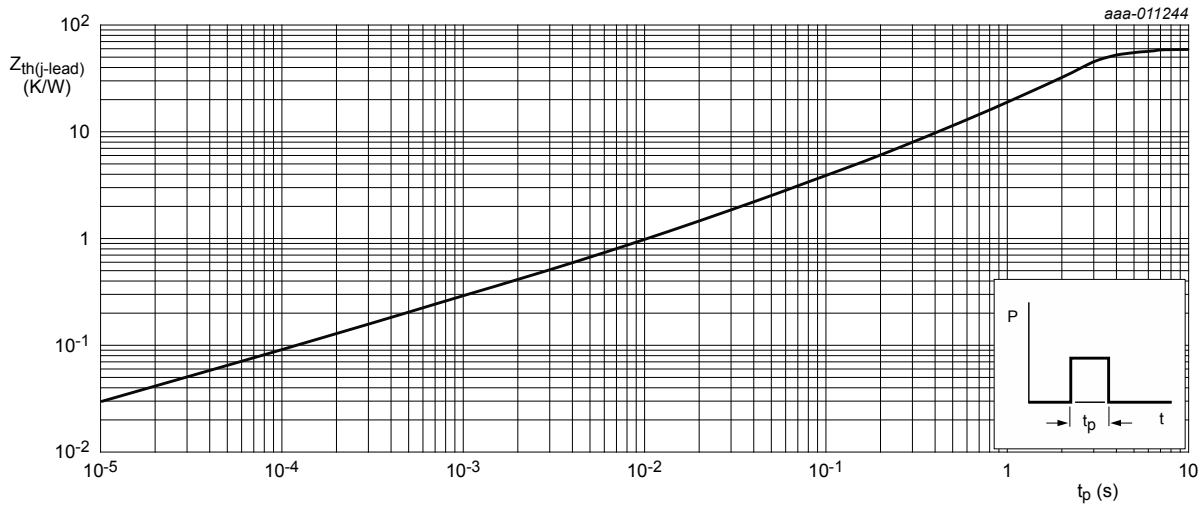
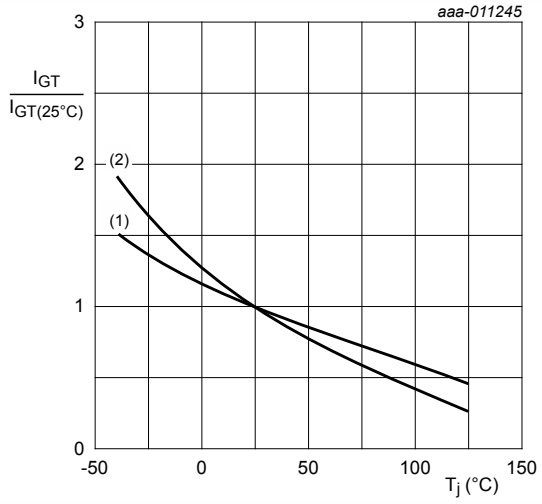


Fig. 7. Transient thermal impedance from junction to lead as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 100 mA; LD+ G-; T_j = 25 °C; Fig. 8		1	-	10	mA
		V_D = 12 V; I_T = 100 mA; LD- G-; T_j = 25 °C; Fig. 8		1	-	10	mA
I_L	latching current	V_D = 12 V; I_G = 100 mA; LD+ G-; T_j = 25 °C; Fig. 9		-	-	25	mA
		V_D = 12 V; I_G = 100 mA; LD- G-; T_j = 25 °C; Fig. 9		-	-	20	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 10		-	-	20	mA
V_T	on-state voltage	I_T = 1.1 A; T_j = 25 °C; Fig. 11		-	-	1.3	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 100 mA; T_j = 25 °C; Fig. 12		-	-	1	V
		V_D = 400 V; I_T = 100 mA; T_j = 125 °C; Fig. 12		0.15	-	-	V
I_D	off-state current	V_D = 800 V; T_j = 25 °C		-	-	2	µA
		V_D = 800 V; T_j = 125 °C		-	-	0.2	mA
V_{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C		850	-	-	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 13		500	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit; Fig. 14; Fig. 15		0.5	-	-	A/ms



(1) LD+ G-
(2) LD- G-

Fig. 8. Normalized gate trigger current as a function of junction temperature

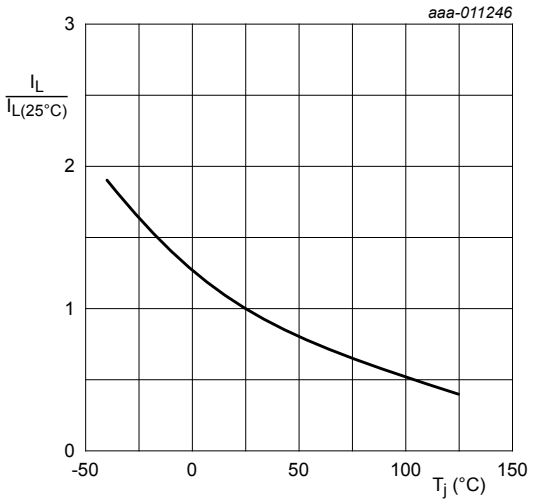


Fig. 9. Normalized latching current as a function of junction temperature

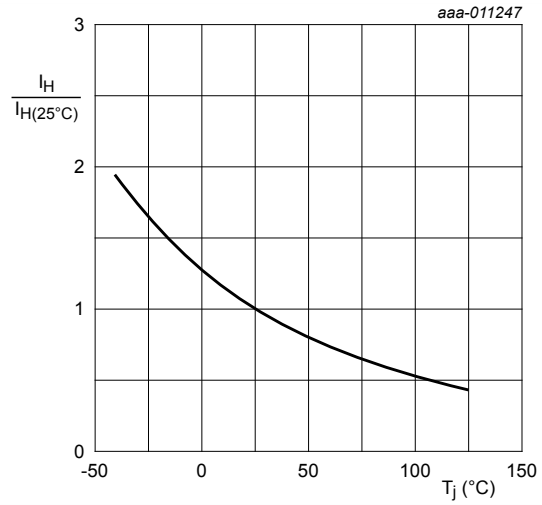
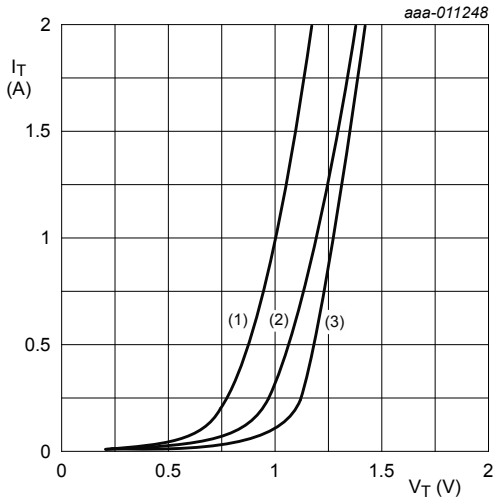


Fig. 10. Normalized holding current as a function of junction temperature



V_o = 0.967 V; R_s = 0.225 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

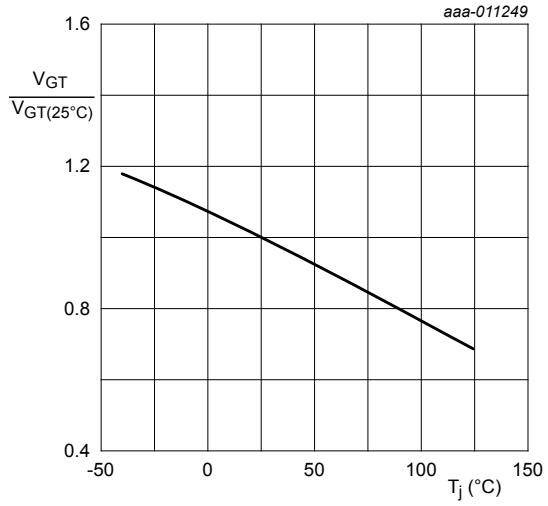
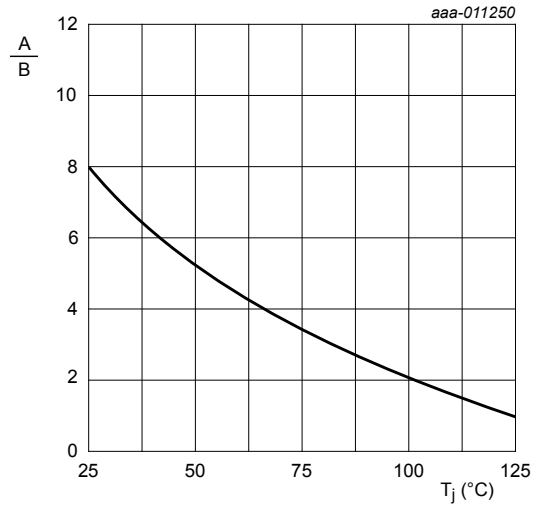


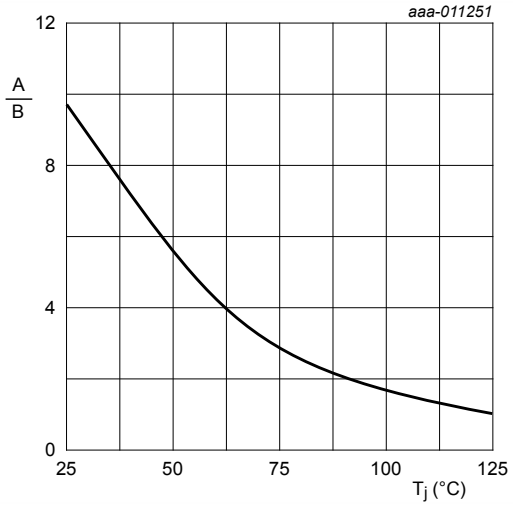
Fig. 12. Normalized gate trigger voltage as a function of junction temperature



A = dV_D/dt at condition T_j °C

B = dV_D/dt at condition T_j [125] °C

Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature

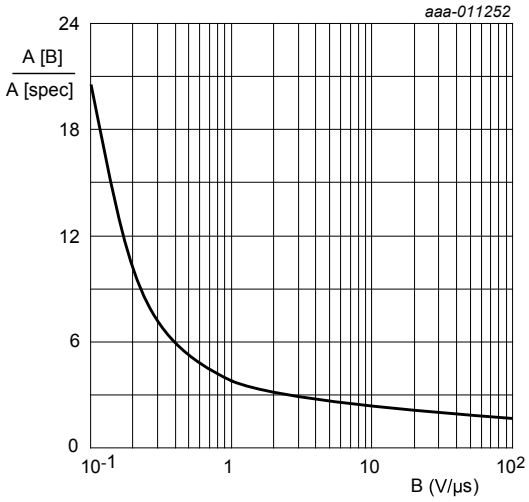


A = dI_{com}/dt at condition T_j °C

B = dI_{com}/dt at condition T_j [125] °C

V_D = 400 V

Fig. 14. Normalized critical rate of rise of commutating current as a function of junction temperature



A [B] = dI_{com}/dt at condition B, dV_{com}/dt

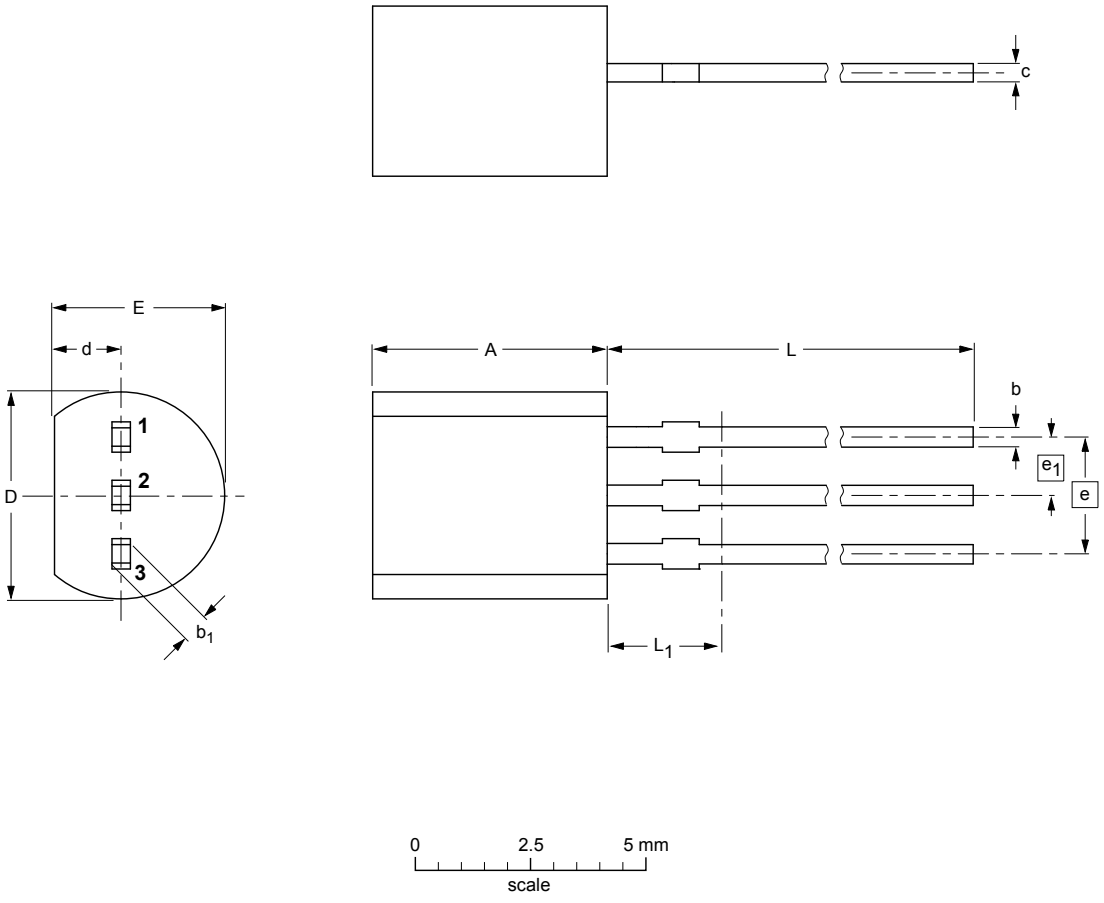
A [spec] is the data sheet value for dI_{com}/dt

turn-off time is less than 20 ms

Fig. 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

10. Package outline

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1 (1) max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			~~04-06-28~~ 04-11-16

Fig. 16. Package outline TO-92 (SOT54)

11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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